

# SN74ACT164-Q1 Automotive Hex D-Type Flip-Flops with Clear

### 1 Features

- AEC-Q100 qualified for automotive applications:
  - Device temperature grade 1: -40°C to +125°C
  - Device HBM ESD classification level 2
  - Device CDM ESD classification level C4B
- Available in wettable flank QFN package
- Operating voltage range of 4.5V to 5.5V
- Continuous ±24mA output drive at 5V
- Supports up to ±75mA output drive at 5V in short bursts
- Drives 50Ω transmission lines
- Fast operation with delay of 14.9ns at 5V

### 2 Applications

- Parallel data synchronization
- Parallel data storage
- Shift register
- Pattern generators

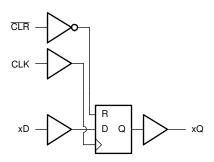
### 3 Description

The SN74ACT164-Q1 device contains six D-type flipflops with shared active-low clear (CLR) and risingedge triggered clock (CLK) inputs.

#### **Device Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE(2)	BODY SIZE(3)
SN74ACT164-Q1	BQB (WQFN, 16)	3.5mm × 2.5mm	3.5mm × 2.5mm
3N/4ACT 104-QT	PW (TSSOP , 16)	5mm x 6.4mm	5mm x 4.4mm

- For more information, see Section 10. (1)
- The package size (length × width) is a nominal value and includes pins, where applicable.
- The body size (length × width) is a nominal value and does not include pins.



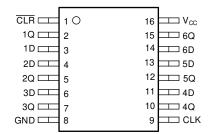
**Functional Diagram** 



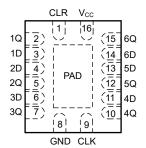
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# **4 Pin Configuration and Functions**



PW Package, 16-Pin TSSOP (Top View)



BQB Package, 16-Pin TSSOP (Transparent Top View)

Table 4-1. Pin Functions

P	IN	TYPE <sup>(1)</sup>	DESCRIPTION					
NO.	NAME	ITPE	DESCRIPTION					
1	CLR	I	Clear all channels, active low					
2	1Q	0	Channel 1, Q output					
3	1D	I	Channel 1, D input					
4	2D	I	Channel 2, D input					
5	2Q	0	Channel 2, Q output					
6	3D	I	Channel 3, D input					
7	3Q	0	Channel 3, Q output					
8	GND	G	Ground					
9	CLK	I	Clock all channels, rising edge triggered					
10	4Q	0	Channel 4, Q output					
11	4D	I	Channel 4, D input					
12	5Q	0	Channel 5, Q output					
13	5D	I	Channel 5, D input					
14	6D	I	Channel 6, D input					
15	6Q	0	Channel 6, Q output					
16	V <sub>CC</sub>	Р	Positive supply					

<sup>(1)</sup> Signal Types: I = Input, O = Output, I/O = Input or Output, P = Power, G = Ground.

### **5 Specifications**

### 5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.5	7	V
VI	Input voltage range <sup>(2)</sup>		-0.5	V <sub>CC</sub> + 0.5V	V
Vo	Output voltage range <sup>(2)</sup>		-0.5	V <sub>CC</sub> + 0.5V	V
I <sub>IK</sub>	Input clamp current	$V_{I} < -0.5V \text{ or } V_{I} > V_{CC} + 0.5V$		±20	mA
I <sub>OK</sub>	Output clamp current	$V_{\rm O}$ < -0.5V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5V		±50	mA
Io	Continuous output current	V <sub>O</sub> = 0 to V <sub>CC</sub>		±50	mA
	Continuous output current through V <sub>CC</sub> or GND			±200	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

#### **5.2 Electrical Characteristics**

over operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST COMPITIONS	V	-40°(	C to 125°C		UNIT	
PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	ONII	
	I - 50A	4.5V	4.4				
	I <sub>OH</sub> = -50μA	5.5V	5.4				
$V_{OH}$	I <sub>OH</sub> = -24mA	4.5V	3.7			V	
	I <sub>OH</sub> = -24mA	5.5V	4.7				
	$I_{OH} = -75 \text{mA}^{(3)}$	5.5V	3.85				
	L = 50A	4.5V			0.1		
	I <sub>OH</sub> = 50μA	5.5V			0.1		
$V_{OL}$	I <sub>OH</sub> = 24mA	4.5V			0.5	V	
	I <sub>OH</sub> = 24mA	5.5V			0.5		
	I <sub>OH</sub> = 75mA <sup>(3)</sup>	5.5V			1.65		
I <sub>I</sub>	V <sub>I</sub> = 5.5V or GND	0V to 5.5V			±1	μA	
l <sub>oz</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	5.5V			±5	μA	
I <sub>cc</sub>	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5V			80	μA	
ΔI <sub>CC</sub>	$V_I = V_{CC} - 2.1V$ ; Any Input	4.5V to 5.5V			1.5	mA	
C <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	5V		8		pF	
Co	V <sub>O</sub> = V <sub>CC</sub> or GND	5V		14		pF	
C <sub>PD</sub> <sup>(1)</sup> <sup>(2)</sup>	C <sub>L</sub> = 50pF, F = 1MHz	5V		60		pF	

<sup>(1)</sup>  $C_{PD}$  is used to determine the dynamic power consumption, per channel

<sup>(2)</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>(2)</sup>  $P_D = V_{CC}^2 x F_1 x (C_{PD} + C_L)$  where  $F_I =$  input frequency,  $C_L =$  output load capacitance,  $V_{CC} =$  supply voltage

<sup>(3)</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed 2 ms.



### 5.3 ESD Ratings

			VALUE	UNIT
Electrostatic	Electrostatio	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 <sup>(1)</sup>	±2000	
V <sub>(ESD)</sub>	discharge	Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	V

(1) AEC Q100-002 indicate that HBM stressing shall be in accordrance with the ANSI/ESDA/JEDEC JS-001 specification.

### **5.4 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	4.5	5.5	V
V <sub>IH</sub>	High-level input voltage	2		V
V <sub>IL</sub>	Low-Level input voltage		0.8	V
VI	Input Voltage	0	V <sub>CC</sub>	V
Vo	Output Voltage	0	Vcc	V
I <sub>OH</sub>	High-level output current		-24	mA
I <sub>OL</sub>	Low-level output current		24	mA
Δt/Δν	Input transition rise or fall rate		20	ns/V
T <sub>A</sub>	Operating free-air temperature	-40	125	°C

### 5.5 Switching Characteristics

 $C_L = 50 \text{ pF}$ ; over operating free-air temperature range; typical values measured at  $T_A = 25^{\circ}\text{C}$  (unless otherwise noted)

DADAMETED	FROM (INDUT)	TO (OUTDUT)	, v		40°C to 125°C		UNIT
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub>	MIN	TYP	MAX	UNII
t <sub>PLH</sub>	CLK	Q	5V			14	ns
t <sub>PHL</sub>	CLK	Q	5V			14	ns
t <sub>PHL</sub>	CLR	Q	5V			15.5	ns

### 5.6 Thermal Information

PACKAGE	PINS			THERMAL	METRIC <sup>(1)</sup>			UNIT
	FINS	R <sub>0JA</sub>	R <sub>0JC(top)</sub>	R <sub>0JB</sub>	$\Psi_{JT}$	$\Psi_{JB}$	R <sub>0JC(bot)</sub>	ONII
PW (TSSOP)	16	126.2	60.5	84.2	7.5	83.3	-	°C/W
BQB (WQFN)	16	91.2	95.1	61.4	18.0	61.2	38.0	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application note.

### **5.7 Timing Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

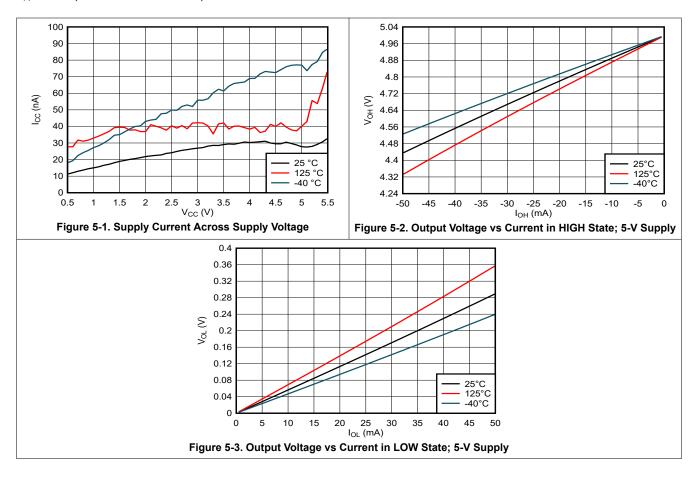
PARAMETER	DESCRIPTION	CONDITION	V	-40°C to 125°C	UNIT
	DESCRIPTION	CONDITION	V <sub>CC</sub>	MIN MAX	
f <sub>CLOCK</sub>	Clock frequency		5V	150	MHz
t <sub>W</sub>	Pulse duration	CLR low	5V	1.5	ns
t <sub>W</sub>	Pulse duration	CLK high or low	5V	1.4	ns
t <sub>SU</sub>	Setup time	Data before CLK↑	5V	1	ns
t <sub>SU</sub>	Setup time	CLR inactive	5V	0.2	ns
t <sub>H</sub>	Hold time	Data after CLK↑	5V	1.1	ns

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### **5.8 Typical Characteristics**

T<sub>A</sub> = 25°C (unless otherwise noted)

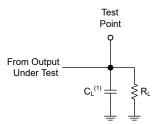


### **6 Parameter Measurement Information**

Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1MHz,  $Z_O$  = 50 $\Omega$ ,  $t_t$  < 2.5ns,  $V_t$  = 1.5V. For push-pull outputs,  $R_L$  = 500 $\Omega$ .

For clock inputs,  $f_{\text{max}}$  is measured when the input duty cycle is 50%.

The outputs are measured individually with one input transition per measurement.



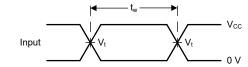


Figure 6-2. Voltage Waveforms, Pulse Duration

(1) C<sub>L</sub> includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for Push-Pull Outputs

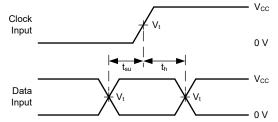
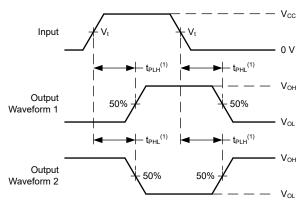
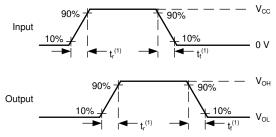


Figure 6-3. Voltage Waveforms, Setup and Hold Times



(1) The greater between  $t_{PLH}$  and  $t_{PHL}$  is the same as  $t_{pd}$ .

Figure 6-4. Voltage Waveforms Propagation Delays



(1) The greater between  $t_{r}$  and  $t_{f}$  is the same as  $t_{t}$ .

Figure 6-5. Voltage Waveforms, Input and Output Transition Times



### 7 Detailed Description

#### 7.1 Overview

The SN74ACT164-Q1 is a positive-edge-triggered hex D-type flip-flop with direct clear ( $\overline{\text{CLR}}$ ) input. Information at the data (D) inputs meeting the setup time requirements is transferred to the outputs on the positive-going edge of the clock (CLK) pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going edge of CLK. When CLK is at either the high or low level, the D input has no effect at the output.

### 7.2 Functional Block Diagram

### 7.3 Feature Description

#### 7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important to limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

### 7.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

#### 7.3.3 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet where packages include this feature.

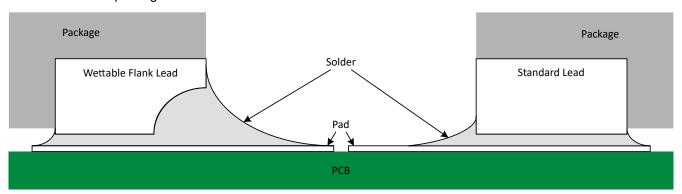


Figure 7-1. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in Figure 7-1, a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

Product Folder Links: SN74ACT174-Q1

### 7.3.4 Clamp Diode Structure

As shown in Figure 7-2, the inputs and outputs to this device have both positive and negative clamping diodes.

#### **CAUTION**

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

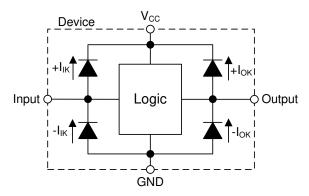


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

### 7.4 Device Functional Modes

Function Table lists the functional modes of the SN74ACT164-Q1.

INPUTS(1) OUTPUT<sup>(2)</sup> **CLR** CLK D Q Χ Χ L Н **↑** Н Н Н L L **↑** Н Χ L  $Q_0$ 

**Table 7-1. Function Table** 

- (1) H = High voltage level, L = Low voltage level, X = Don't care, ↑ = Low to High transition
- (2)  $Q_0 = \text{Previous output state (High or Low)}$



### 8 Application and Implementation

#### **Note**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### **8.1 Application Information**

The SN74ACT164-Q1 contains multiple D-type flip-flops that are operated by the same clock. By connecting multiple channels together in series, a shift register can be formed. This produces a delay of a specific number of clock cycles for incoming data. The application schematic shown below gives an example of using three channels of the SN74ACT164-Q1 to produce a delay of three clock cycles.

At startup, the output states are unknown and must be cleared before beginning operation.

### 8.2 Typical Application

Product Folder Links: SN74ACT174-Q1



### 8.2.1 Design Requirements

#### 8.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics of the device as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74ACT164-Q1 plus the maximum static supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Ensure the maximum total current through  $V_{CC}$  listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74ACT164-Q1 plus the maximum supply current, I<sub>CC</sub>, listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Ensure the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74ACT164-Q1 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50pF.

The SN74ACT164-Q1 can drive a load with total resistance described by  $R_L \ge V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the  $V_{CC}$  pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear* and Logic (SLL) Packages and Devices.

#### **CAUTION**

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.



#### 8.2.1.2 Input Considerations

Input signals must cross to be considered a logic LOW, and to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74ACT164-Q1 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A  $10k\Omega$  resistor value is often used due to these factors.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

#### 8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

Product Folder Links: SN74ACT174-Q1

### 8.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the *Layout* section.
- Ensure the capacitive load at the output is ≤ 50pF. This is not a hard limit; by design, however, it will
  optimize performance. This can be accomplished by providing short, appropriately sized traces from the
  SN74ACT164-Q1 to one or more of the receiving devices.
- 3. Ensure the resistive load at the output is larger than  $(V_{CC} / I_{O(max)})\Omega$ . Doing this will prevent the maximum output current from the *Absolute Maximum Ratings* from being violated. Most CMOS inputs have a resistive load measured in M $\Omega$ ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

### 8.2.3 Application Curve

### 8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V<sub>CC</sub> terminal should have a good bypass capacitor to prevent power disturbance. A 0.1µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. The 0.1µF and 1µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

#### 8.4 Layout

### 8.4.1 Layout Guidelines

- · Bypass capacitor placement
  - Place near the positive supply terminal of the device
  - Provide an electrically short ground return path
  - Use wide traces to minimize impedance
  - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
  - 8mil to 12mil trace width
  - Lengths less than 12cm to minimize transmission line effects
  - Avoid 90° corners for signal traces
  - Use an unbroken ground plane below signal traces
  - Flood fill areas around signal traces
  - For traces longer than 12cm
    - · Use impedance controlled traces
    - Source-terminate using a series damping resistor near the output
    - · Avoid branches; buffer signals that must branch separately



### 8.4.2 Layout Example

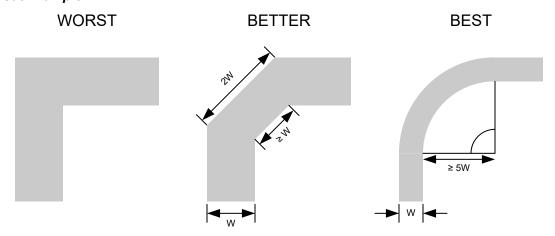


Figure 8-1. Example Trace Corners for Improved Signal Integrity

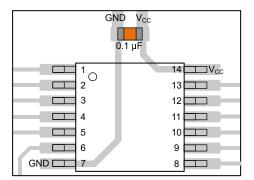


Figure 8-2. Example Bypass Capacitor Placement for TSSOP and Similar Packages

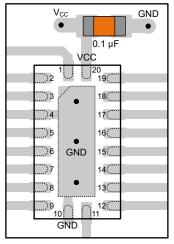


Figure 8-3. Example Bypass Capacitor Placement for WQFN and Similar Packages

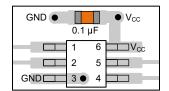


Figure 8-4. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

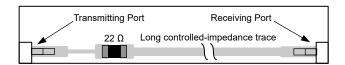


Figure 8-5. Example Damping Resistor Placement for Improved Signal Integrity

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### 9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

### 9.1 Documentation Support

#### 9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report
- Texas Instruments, *Designing With Logic* application report
- Texas Instruments, Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices application report

### 9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 9.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 9.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

### 9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 9.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

### 10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
October 2024	*	Initial release

# 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74ACT174PWRQ1	ACTIVE	TSSOP	PW	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	ACT174Q	Samples
SN74ACT174WBQBRQ1	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AD174Q	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

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# **PACKAGE MATERIALS INFORMATION**

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### TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74ACT174PWRQ1	TSSOP	PW	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74ACT174WBQBRQ1	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1

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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74ACT174PWRQ1	TSSOP	PW	16	3000	353.0	353.0	32.0
SN74ACT174WBQBRQ1	WQFN	BQB	16	3000	210.0	185.0	35.0



SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



2.5 x 3.5, 0.5 mm pitch

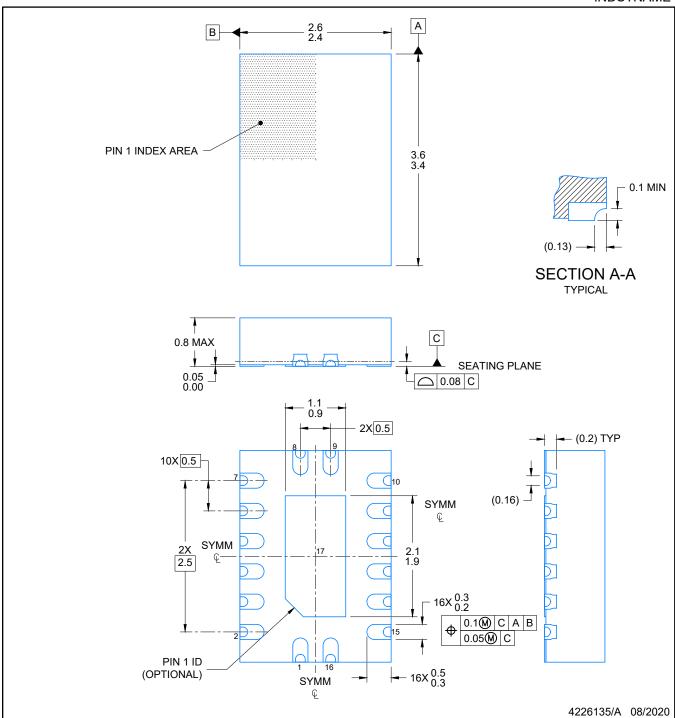
PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



**INSTRUMENTS** www.ti.com

**INDSTNAME** 

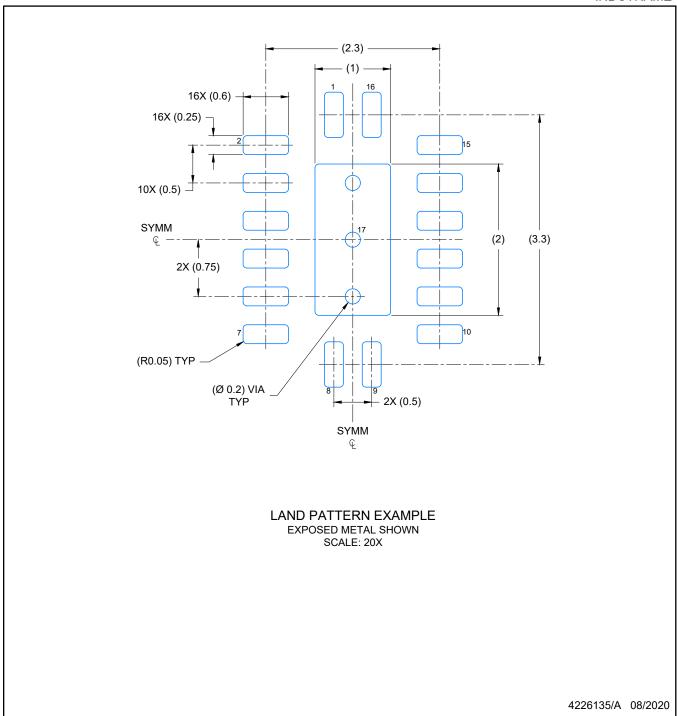


#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



**INDSTNAME** 

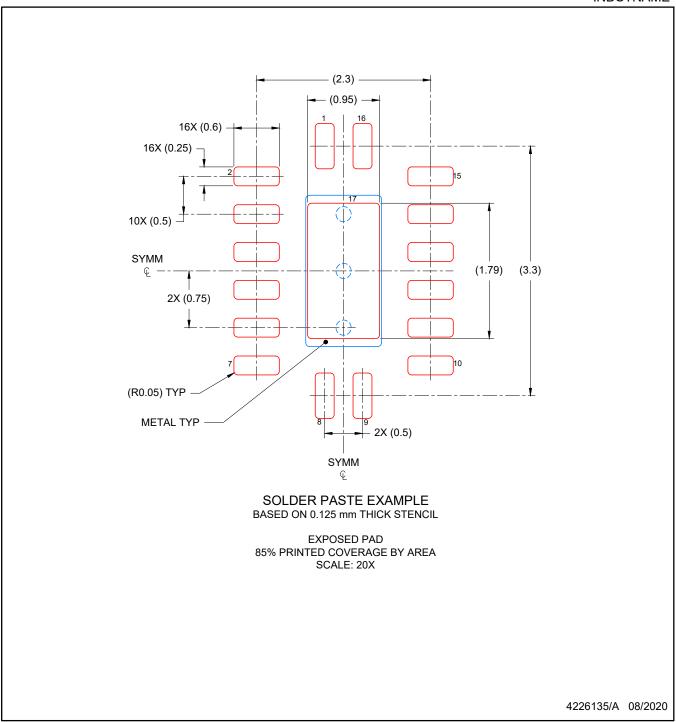


#### NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



**INDSTNAME** 



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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